

PMEG2010EPK

20 V, 1 A low VF MEGA Schottky barrier rectifier Rev. 2 — 14 March 2012

Product data sheet

Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small SOD1608 (DFN1608D-2) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

1.2 Features and benefits

- Average forward current: I_{F(AV)} ≤ 1 A
- Reverse voltage: V_R ≤ 20 V
- Low forward voltage V_F ≤ 415 mV
- Low reverse current

- AEC-Q101 qualified
- Solderable side pads
- Package height typ. 0.37 mm
- Ultra small and leadless SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- LED backlight for mobile application
- Low power consumption applications
- Ultra high-speed switching
- Reverse polarity protection

1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions		Min	Тур	Max	Unit
average forward current	square wave; δ = 0.5; f = 20 kHz; T _{amb} ≤ 110 °C	<u>[1]</u>	-	-	1	Α
	square wave; δ = 0.5; f = 20 kHz; T _{sp} ≤ 135 °C		-	-	1	Α
reverse voltage	T _j = 25 °C		-	-	20	V
forward voltage	I_F = 1 A; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_j = 25 °C		-	370	415	mV
reverse current	V _R = 10 V; T _j = 25 °C		-	50	250	μA
reverse recovery time	$I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 ^{\circ}\text{C}$		-	4	-	ns
	average forward current reverse voltage forward voltage reverse current	$\begin{array}{ll} \text{average forward} & \text{square wave; } \delta = 0.5; f = 20 \text{kHz;} \\ T_{amb} \leq 110 ^{\circ}\text{C} \\ & \text{square wave; } \delta = 0.5; f = 20 \text{kHz;} \\ T_{sp} \leq 135 ^{\circ}\text{C} \\ \\ \text{reverse voltage} & T_{j} = 25 ^{\circ}\text{C} \\ \\ \text{forward voltage} & I_{F} = 1 \text{A; pulsed; } t_{p} \leq 300 \mu\text{s; } \delta \leq 0.02; \\ T_{j} = 25 ^{\circ}\text{C} \\ \\ \text{reverse current} & V_{R} = 10 \text{V; } T_{j} = 25 ^{\circ}\text{C} \\ \\ \text{reverse recovery time} & I_{R} = 0.5 \text{A; } I_{R(meas)} = 0.1 \text{A;} \\ \end{array}$	$\begin{array}{ll} \text{average forward} & \text{square wave; } \delta = 0.5; f = 20 \text{kHz;} \\ T_{amb} \leq 110 ^{\circ}\text{C} \\ \hline \text{square wave; } \delta = 0.5; f = 20 \text{kHz;} \\ T_{sp} \leq 135 ^{\circ}\text{C} \\ \hline \text{reverse voltage} & T_{j} = 25 ^{\circ}\text{C} \\ \hline \text{forward voltage} & I_{F} = 1 \text{A; pulsed; } t_{p} \leq 300 \mu\text{s; } \delta \leq 0.02; \\ T_{j} = 25 ^{\circ}\text{C} \\ \hline \text{reverse current} & V_{R} = 10 \text{V; } T_{j} = 25 ^{\circ}\text{C} \\ \hline \text{reverse recovery time} & I_{R} = 0.5 \text{A; } I_{R(meas)} = 0.1 \text{A;} \\ \hline \end{array}$	$\begin{array}{lll} \text{average forward} & \text{square wave; } \delta = 0.5; f = 20 \text{kHz;} & \\ \hline T_{amb} \leq 110 ^{\circ}\text{C} & \\ \hline \text{square wave; } \delta = 0.5; f = 20 \text{kHz;} & \\ \hline T_{sp} \leq 135 ^{\circ}\text{C} & \\ \hline \text{reverse voltage} & T_{j} = 25 ^{\circ}\text{C} & \\ \hline \text{forward voltage} & I_{F} = 1 \text{A; pulsed; } t_{p} \leq 300 \text{\mus; } \delta \leq 0.02; \\ \hline T_{j} = 25 ^{\circ}\text{C} & \\ \hline \text{reverse current} & V_{R} = 10 \text{V; } T_{j} = 25 ^{\circ}\text{C} & \\ \hline \text{reverse recovery time} & I_{R} = 0.5 \text{A; } I_{R(meas)} = 0.1 \text{A;} & \\ \hline \end{array}$	$\begin{array}{c} \text{average forward} \\ \text{current} \\ \end{array} \begin{array}{c} \text{square wave; } \delta = 0.5; f = 20 \text{ kHz;} \\ T_{amb} \leq 110 ^{\circ}\text{C} \\ \end{array} \\ \text{square wave; } \delta = 0.5; f = 20 \text{ kHz;} \\ T_{sp} \leq 135 ^{\circ}\text{C} \\ \end{array} \\ \text{reverse voltage} \\ T_{j} = 25 ^{\circ}\text{C} \\ \text{forward voltage} \\ T_{j} = 1 \text{A; pulsed; } t_{p} \leq 300 \text{\mus; } \delta \leq 0.02; \\ T_{j} = 25 ^{\circ}\text{C} \\ \end{array} \\ \text{reverse current} \\ V_{R} = 10 \text{V; } T_{j} = 25 ^{\circ}\text{C} \\ \text{reverse recovery time} \\ I_{R} = 0.5 \text{A; } I_{R(meas)} = 0.1 \text{A;} \\ \end{array} \\ \begin{array}{c} 11 \\ - \\ - \\ 50 \\ \end{array} \\ \end{array}$	$\begin{array}{llllllllllllllllllllllllllllllllllll$

^[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]		. 84 .
2	Α	anode	1 2	1 2 sym001
			Transparent top view	
			SOD1608 (DFN1608D-2))

^[1] The marking bar indicates the cathode.

3. Ordering information

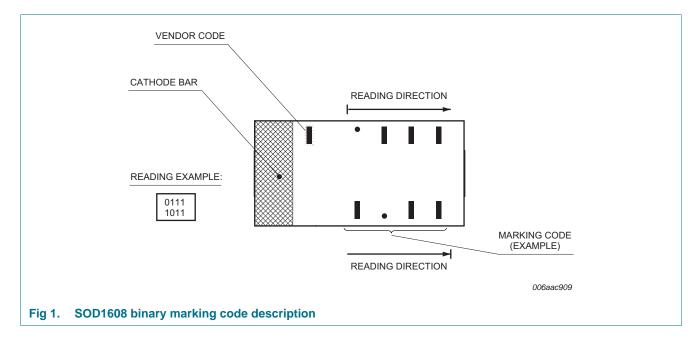
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG2010EPK	DFN1608D-2	Leadless ultra small plastic package; 2 terminals	SOD1608

4. Marking

Table 4. Marking codes

Type number	Marking code
PMEG2010EPK	0100 0000



5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	$T_j = 25 ^{\circ}C$		-	20	V
I _F	forward current	T _{sp} ≤ 130 °C		-	1.4	Α
I _{F(AV)}	average forward current	square wave; δ = 0.5; f = 20 kHz; T _{amb} ≤ 110 °C	<u>[1]</u>	-	1	Α
		square wave; δ = 0.5; f = 20 kHz; T _{sp} ≤ 135 °C		-	1	Α
I_{FRM}	repetitive peak forward current	$t_p \le 1 \text{ ms}; \ \delta \le 0.25$		-	3	Α
I _{FSM}	non-repetitive peak forward current	square wave; $t_p = 8 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$		-	5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	410	mW
			[3]	-	860	mW
			[1]	-	1565	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fr	thermal resistance	in free air	[1][2]	-	-	305	K/W
	from junction to ambient		[1][3]	-	-	145	K/W
	ambient		[1][4]	-	-	80	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[5]</u>	-	-	20	K/W

^[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

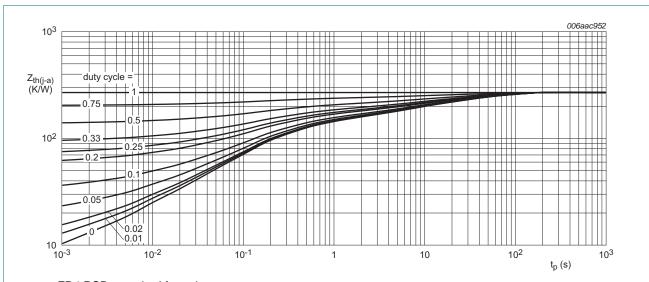
^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

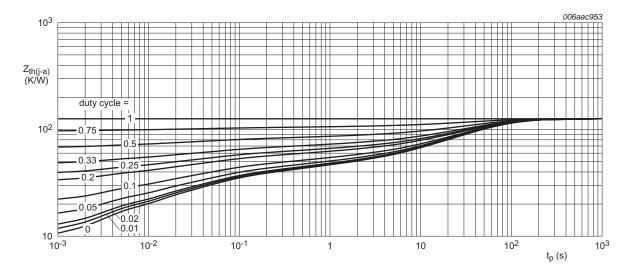
^[4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

^[5] Soldering point of cathode tab.



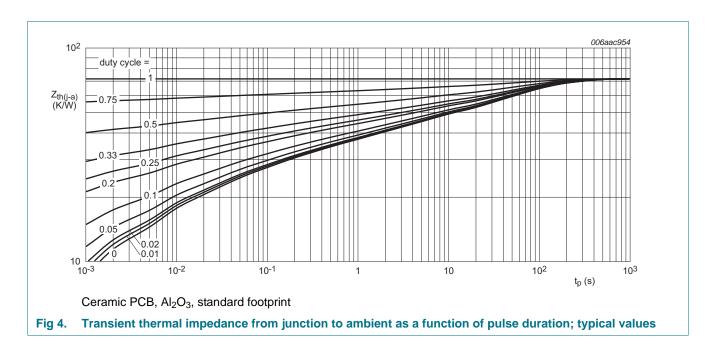
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm²

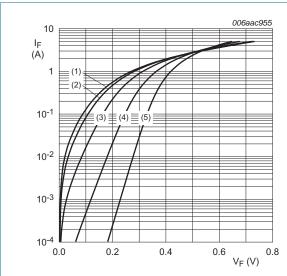
Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage	I_F = 100 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_j = 25 °C	-	240	280	mV
		I_F = 500 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_j = 25 °C	-	310	350	mV
		I_F = 700 mA; pulsed; $t_p \le 300 \mu s$; $δ \le 0.02$; T_j = 25 °C	-	330	390	mV
		I_F = 1 A; pulsed; $t_p \le 300 \text{ μs}$; $\delta \le 0.02$; T_j = 25 °C	-	370	415	mV
I _R reverse current	reverse current	V _R = 10 V; T _j = 25 °C	-	50	250	μA
		V _R = 20 V; T _j = 25 °C	-	150	600	μΑ
C _d	diode capacitance	$V_R = 1 \text{ V; } f = 1 \text{ MHz; } T_j = 25 \text{ °C}$	-	65	-	pF
		$V_R = 10 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ °C}$	-	25	-	pF
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	4	-	ns
V_{FRM}	peak forward recovery voltage	$I_F = 0.5 \text{ A}; dI_F/dt = 20 \text{ A/}\mu\text{s}; T_j = 25 \text{ °C}$	-	335	-	mV



- (1) $T_i = 150 \, ^{\circ}C$
- (2) $T_i = 125 \, ^{\circ}C$
- (3) $T_i = 85 \, ^{\circ}C$
- (4) $T_j = 25 \, ^{\circ}C$
- (5) $T_j = -40 \, ^{\circ}C$

Fig 5. Forward current as a function of forward voltage; typical values

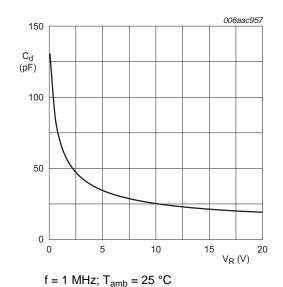
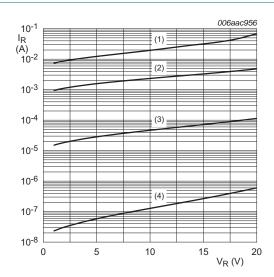
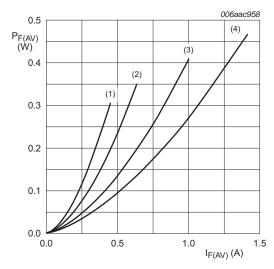


Fig 7. Diode capacitance as a function of reverse voltage; typical values



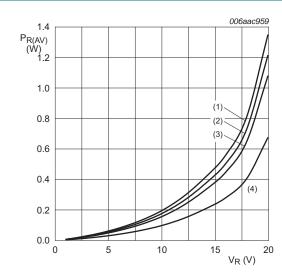
- (1) $T_i = 125 \, ^{\circ}C$
- (2) $T_i = 85 \, ^{\circ}C$
- (3) $T_j = 25 \, {}^{\circ}\text{C}$
- (4) $T_i = -40 \, ^{\circ}C$

Fig 6. Reverse current as a function of reverse voltage; typical values



- T_i = 150 °C
- (1) $\delta = 0.1$
- (2) $\delta = 0.2$
- (3) $\delta = 0.5$
- (4) $\delta = 1$

Fig 8. Average forward power dissipation as a function of average forward current; typical values



T_i = 125 °C

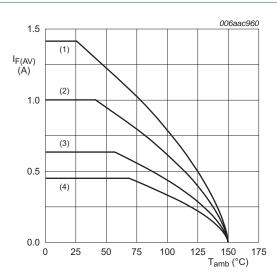
(1) $\delta = 1$

(2) $\delta = 0.9$

(3) $\delta = 0.8$

(4) $\delta = 0.5$

Fig 9. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

 $T_i = 150 \, ^{\circ}C$

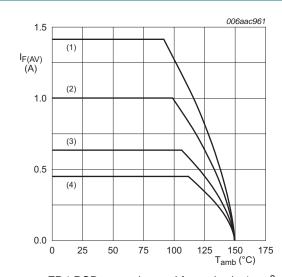
(1) $\delta = 1$ (DC)

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig 10. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

T_i = 150 °C

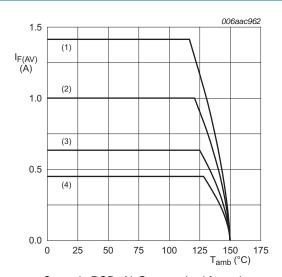
(1) $\delta = 1$ (DC)

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig 11. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

 $T_i = 150 \, ^{\circ}C$

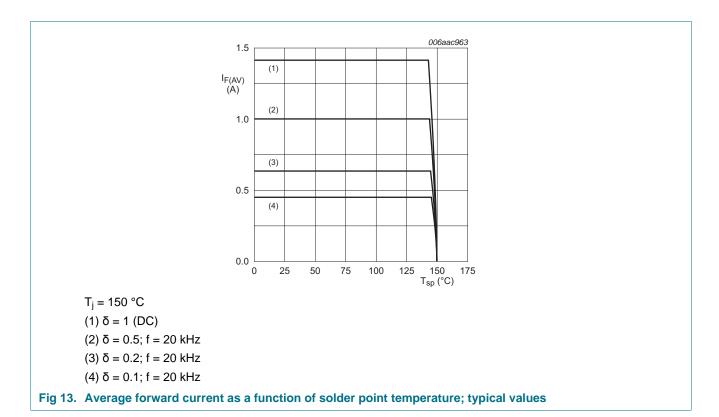
(1) $\delta = 1$ (DC)

(2) $\delta = 0.5$; f = 20 kHz

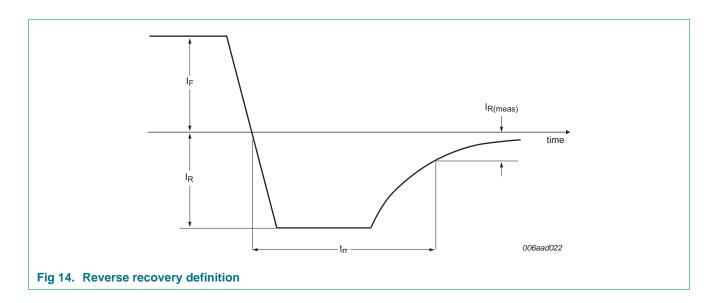
(3) $\delta = 0.2$; f = 20 kHz

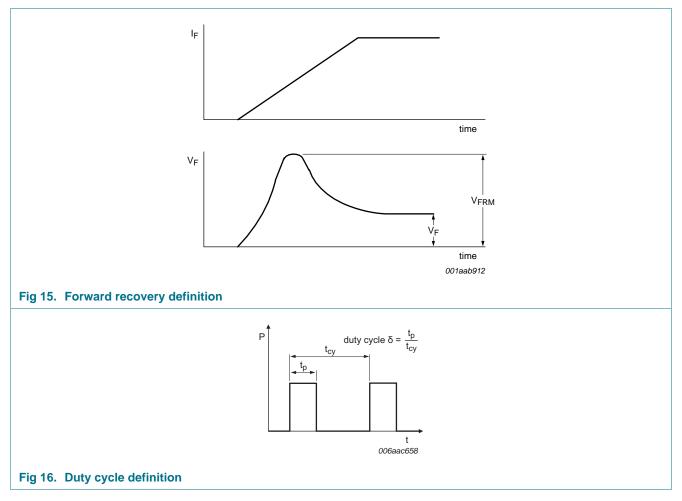
(4) $\delta = 0.1$; f = 20 kHz

Fig 12. Average forward current as a function of ambient temperature; typical values



8. Test information



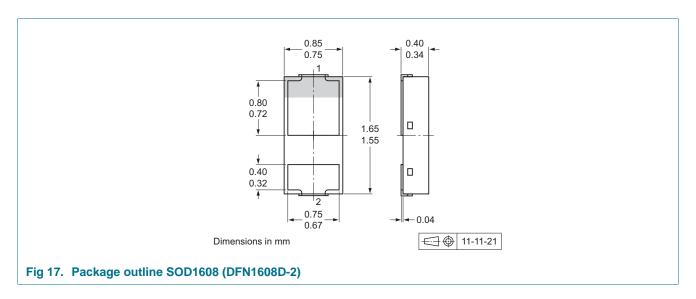


The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

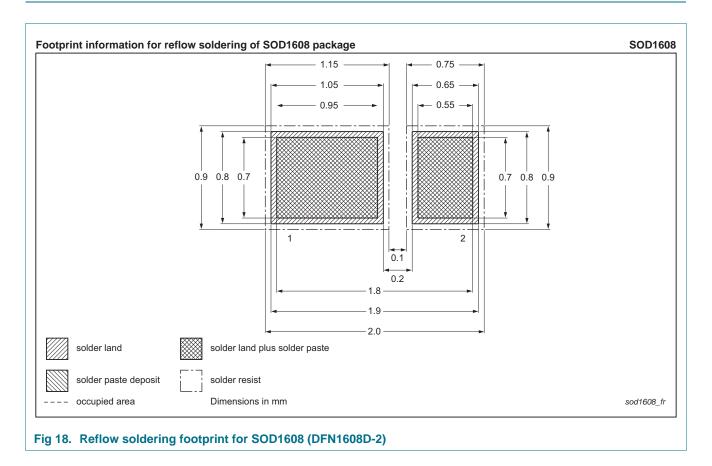
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline



10. Soldering





11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
Document 15	residude date	Data officer otatao	Change notice	ouperocues -
PMEG2010EPK v.2	20120314	Product data sheet	-	PMEG2010EPK v.1
Modifications:	• 5 "Limiting va	lues": I _F corrected		
	• 7 "Characteris	stics": t _{rr} and V _{FRM} added		
	• <u>Fig 14.</u> and <u>1</u>	<u>5</u> : added		
PMEG2010EPK v.1	20120120	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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